

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
	100mΩ @ V _{GS} = -4.5V	-2.0A
-20V	120mΩ @ V _{GS} = -2.5V	-1.9A
	160mΩ @ V _{GS} = -1.8V	-1.6A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

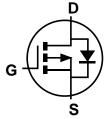
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish—Matte Tin Annealed over Alloy 42 Leadframe.
 Solderable per MIL-STD-202, Method 208@3
- Weight: 0.006 grams (Approximate)

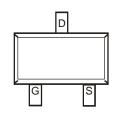




Top View



Internal Schematic



Top View

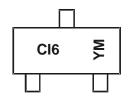
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2110UW-7	SOT323	3000/Tape & Reel
DMP2110UW-13	SOT323	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



CI6 = Marking Code YM = Date Code Marking \overline{Y} = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2018		2019	2020		2021	2022		2023	2024		2025
Code	F		G	Н		1	J		K	L		M
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	I _D	-2.0 -1.6	А	
Maximum Continuous Body Diode Forward Curren	t (Note 6)	Is	-0.9	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	%) (Note 6)	I _{DM}	-15	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	0.49	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	253	°C/W
Total Power Dissipation (Note 6)	P _D	0.65	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	192	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

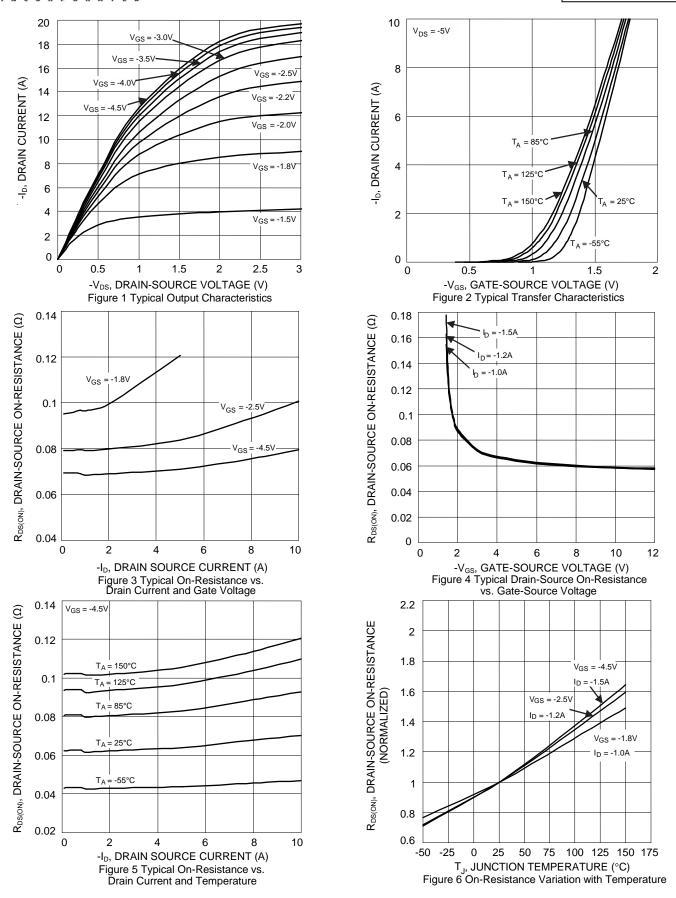
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	lass	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±800	IIA	$V_{GS} = \pm 12V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-0.4	_	-0.9	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
			63	100		$V_{GS} = -4.5V, I_D = -1.5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	75	120	$m\Omega$	$V_{GS} = -2.5V, I_D = -1.2A$	
			89	160		$V_{GS} = -1.8V, I_D = -1A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -1.0A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	443	_	pF		
Output Capacitance	Coss	_	59	_	pF	$V_{DS} = -6V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	47	_	pF	1 - 1.01/11/2	
Gate Resistance	R_{G}	_	8.5	_	Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$	
Total Gate Charge	Qg	_	6.0	_	nC		
Gate-Source Charge	Q _{gs}	_	0.6	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -3A$	
Gate-Drain Charge	Q_{gd}	_	1.8	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	4.0	_	ns		
Turn-On Rise Time	t _R	_	3.7	_	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	24.5	_	ns	$R_L = 10\Omega, R_G = 1.0\Omega, I_D = -1A$	
Turn-Off Fall Time	t _F	_	9.5	_	ns]	
Reverse Recovery Time	t _{RR}	_	8.3	_	ns	I _F = -1.0A, di/dt = 100A/μs	
Reverse Recovery Charge	Q _{RR}	_	2.0	_	nC	I _F = -1.0A, di/dt = 100A/µs	

Notes:

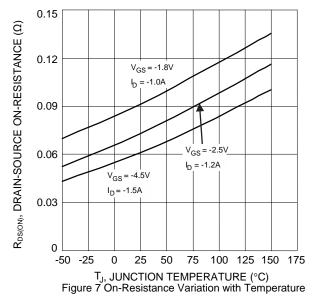
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

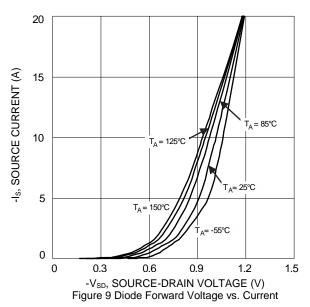


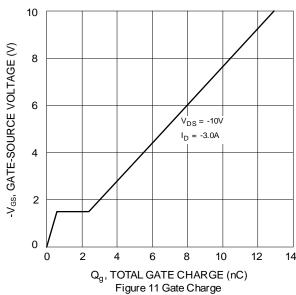












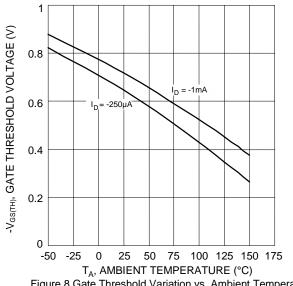
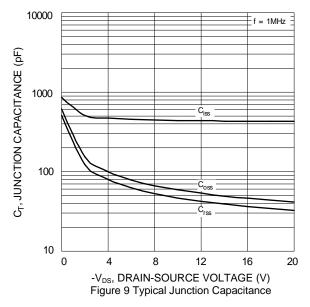


Figure 8 Gate Threshold Variation vs. Ambient Temperature



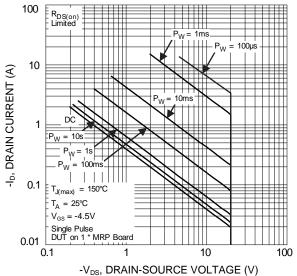
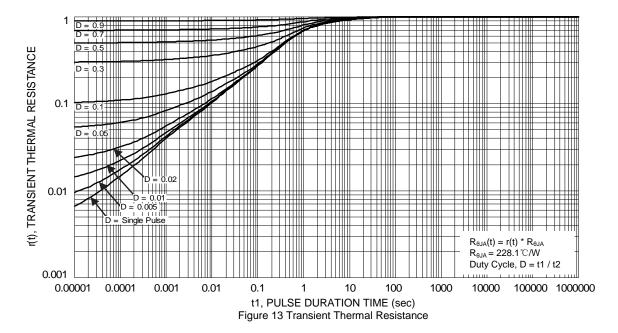


Figure 12 SOA, Safe Operation Area



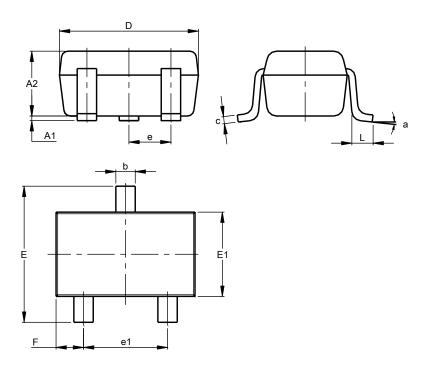




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323

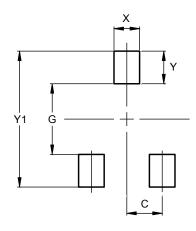


	SOT323							
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.25	0.40	0.30					
C	0.10	0.18	0.11					
D	1.80	2.20	2.15					
Е	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	C).650 B	SC					
e1	1.20	1.40	1.30					
F	0.375	0.475	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323



Dimensions	Value
Dilliensions	(in mm)
С	0.650
G	1.300
Х	0.470
Υ	0.600
Y1	2.500



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